

General Description

The WSR200N08 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications.

The WSR200N08 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summary

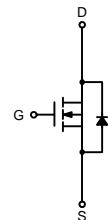
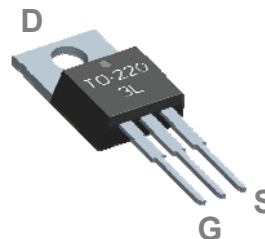
BV _{DSS}	R _{DS(on)}	I _D
80V	2.9mΩ	200A

Applications

Switching application

Power Management for Inverter Systems.

TO-220FB-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	80	V
V _{GS}	Gate-Source Voltage	±25	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	200	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	144	A
I _{DM}	Pulsed Drain Current ² , T _C =25°C	790	A
EAS	Avalanche Energy, Single pulse, L=0.5mH	1496	mJ
I _{AS}	Avalanche Current, Single pulse, L=0.5mH	200	A
P _D @T _C =25°C	Total Power Dissipation ⁴	345	W
P _D @T _C =100°C	Total Power Dissipation ⁴	173	W
T _{STG}	Storage Temperature Range	-55 to 175	°C
T _J	Operating Junction Temperature Range	175	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	62.5	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	0.43	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	80	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.096	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =100A	---	2.9	3.5	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2.0	3.0	4.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.5	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	10	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±25V, V _{DS} =0V	---	---	±100	nA
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	3.2	---	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =80V, V _{GS} =10V, I _D =30A	---	197	---	nC
Q _{gs}	Gate-Source Charge		---	31	---	
Q _{gd}	Gate-Drain Charge		---	75	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =50V, V _{GS} =10V, R _G =3Ω, I _D =30A	---	28	---	ns
T _r	Rise Time		---	18	---	
T _{d(off)}	Turn-Off Delay Time		---	42	---	
T _f	Fall Time		---	54	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	8154	---	pF
C _{oss}	Output Capacitance		---	1029	---	
C _{rss}	Reverse Transfer Capacitance		---	650	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =25V, L=0.5mH, I _{AS} =28A	160	---	---	mJ

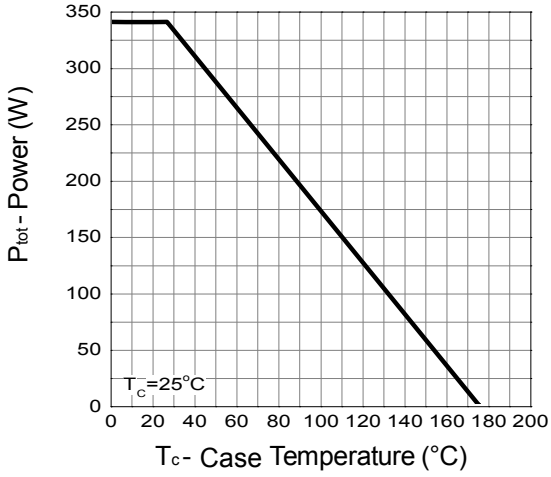
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	200	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	350	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =15A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =15A, dI/dt=100A/μs, T _J =25°C	---	30	---	nS
Q _{rr}	Reverse Recovery Charge		---	52	---	nC

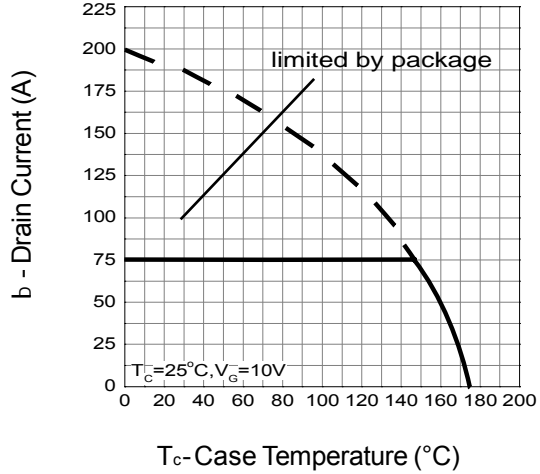
Note * : Pulse test ; pulse width ≤300μs, duty cycle ≤2%.

Typical Operating Characteristics

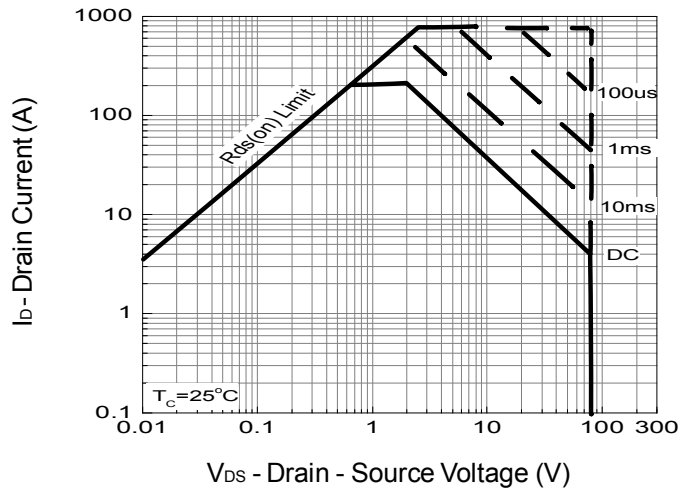
Power Dissipation



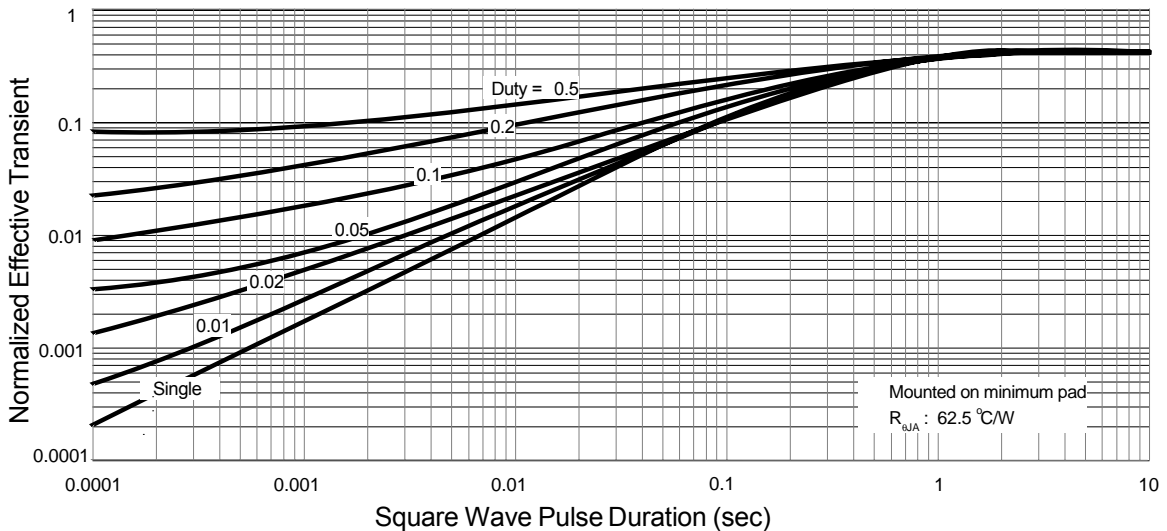
Drain Current



Safe Operation Area

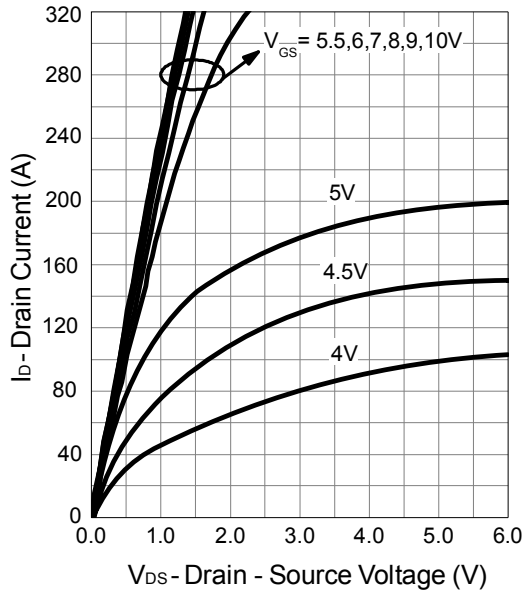


Thermal Transient Impedance

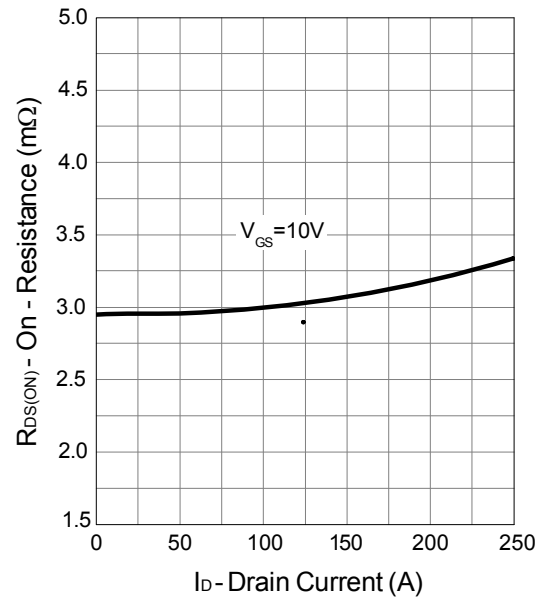


Typical Operating Characteristics (Cont.)

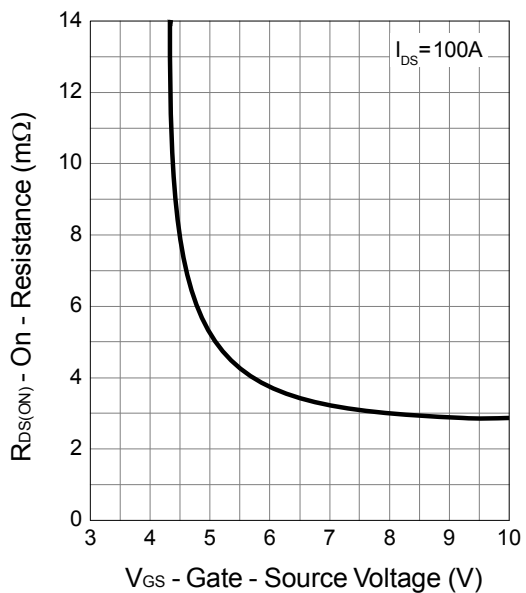
Output Characteristics



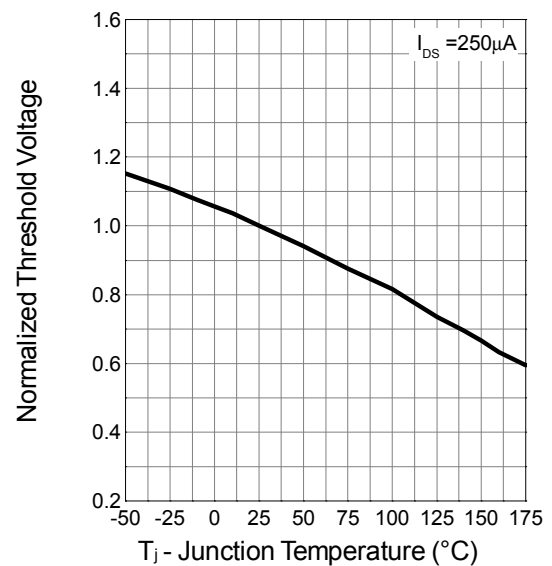
Drain-Source On Resistance



Gate-Source On Resistance

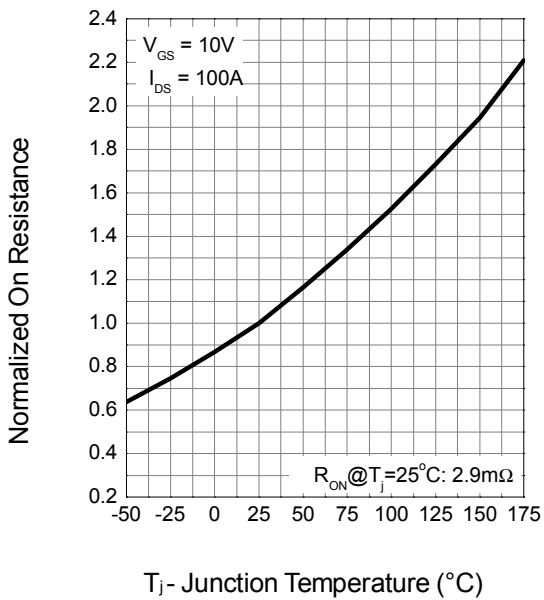


Gate Threshold Voltage

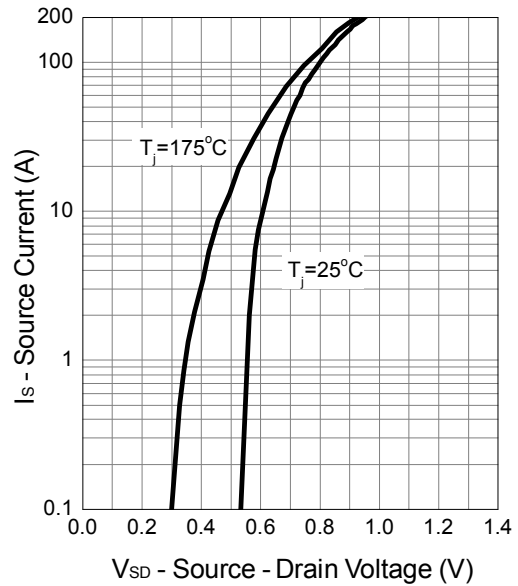


Typical Operating Characteristics (Cont.)

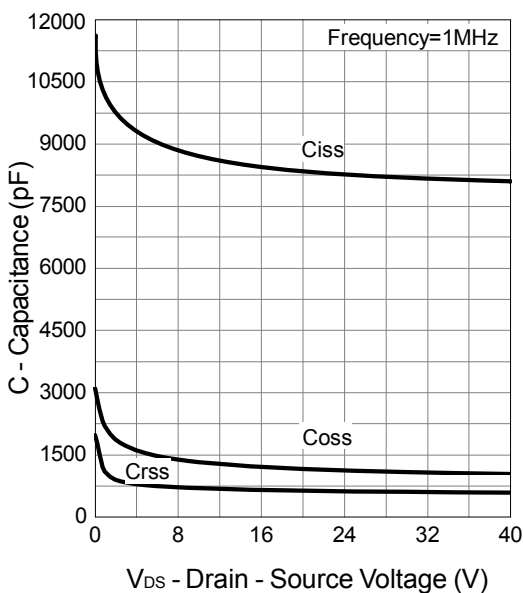
Drain-Source On Resistance



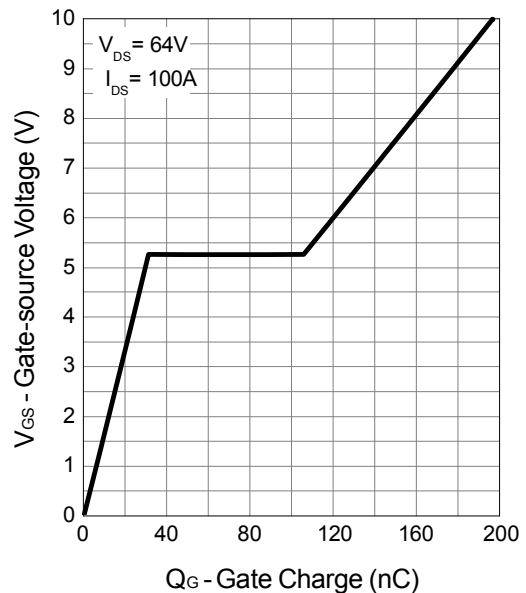
Source-Drain Diode Forward



Capacitance



Gate Charge





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